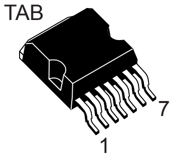
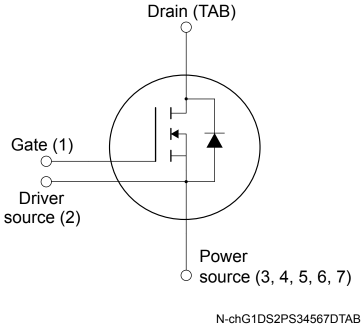
SCT018H65G3-7

Datasheet

Silicon carbide Power MOSFET 650 V, 20 mΩ typ., 55 A in an H²PAK-7 package



H²PAK-7



Product status link
SCT018H65G3-7

Product summary	
Order code	SCT018H65G3-7
Marking	18H65G3
Package	H²PAK-7
Packing	Tape and reel

Features

Order code	V_{DS}	$R_{DS(on)}$ typ.	I_D
SCT018H65G3-7	650 V	20 mΩ	55 A

- Very fast and robust intrinsic body diode
- Very low $R_{DS(on)}$ over the entire temperature range
- High speed switching performances
- Source sensing pin for increased efficiency

Applications

- Switching mode power supply
- Power supply for renewable energy systems
- DC-DC converters

Description

This silicon carbide Power MOSFET device has been developed using ST's advanced and innovative 3rd generation SiC MOSFET technology. The device features a very low $R_{DS(on)}$ over the entire temperature range combined with low capacitances and very high switching operations, which improve application performance in frequency, energy efficiency, system size and weight reduction.

1 Electrical ratings

Table 1. **Absolute maximum ratings**

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	650	V
V_{GS}	Gate-source voltage	-10 to 22	V
	Gate-source voltage (recommended operating values)	-5 to 18	
	Gate-source transient voltage, $t_p < 1$ µs, $t \leq 10$ hours over lifetime	-11 to 25	
I_D[1]	Drain current (continuous) at $T_C = 25$ °C	55	A
	Drain current (continuous) at $T_C = 100$ °C	55	
I_{DM}[2]	Drain current (pulsed)	312	A
P_{TOT}	Total power dissipation at $T_C = 25$ °C	385	W
T_{stg}	Storage temperature range	-55 to 175	°C
T_J	Operating junction temperature range		°C

1. *I_D is limited by package.*
2. *Pulse width is limited by safe operating area.*

Table 2. **Thermal data**

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.39	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	650			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 650 V			10	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = -10 to 22 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 5 mA	1.8	3.0	4.2	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 15 V, I_D = 30 A		24		mΩ
		V_{GS} = 18 V, I_D = 30 A		20	27	
		V_{GS} = 18 V, I_D = 30 A, T_J = 175 °C		28		

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 400 V, f = 1 MHz, V_{GS} = 0 V	-	2124	-	pF
C_{oss}	Output capacitance		-	184	-	pF
C_{rss}	Reverse transfer capacitance		-	18	-	pF
Q_g	Total gate charge	V_{DD} = 400 V, V_{GS} = -5 to 18 V, I_D = 30 A	-	79.4	-	nC
Q_{gs}	Gate-source charge		-	23.5	-	nC
Q_{gd}	Gate-drain charge		-	20.3	-	nC
R_g	Gate input resistance	f = 1 MHz, I_D = 0 A	-	1.14	-	Ω

Table 5. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	V_{DD} = 400 V, I_D = 30 A, R_G = 18 Ω, V_{GS} = -5 V to 18 V	-	209	-	µJ
E_{off}	Turn-off switching energy		-	184	-	µJ

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 400 V, I_D = 30 A, R_G = 18 Ω, V_{GS} = -5 to 18 V	-	25	-	ns
t_r	Rise time		-	28	-	ns
$t_{d(off)}$	Turn-off delay time		-	56	-	ns
t_f	Fall time		-	25	-	ns

Table 7. **Reverse SiC diode characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}(1)	Continuous diode forward current	T_C = 25 °C	-		55	A
		T_C = 100 °C	-		55	
V_{SD}	Diode forward voltage	I_{SD} = 30 A, V_{GS} = 0 V	-	2.6		V
t_{rr}	Reverse recovery time	I_{SD} = 30 A, di/dt = 1000 A/µs, V_{DD} = 400 V	-	20		ns
Q_{rr}	Reverse recovery charge		-	147		nC
I_{RRM}	Reverse recovery current		-	11.8		A

1. *I_{SD} is limited by package.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

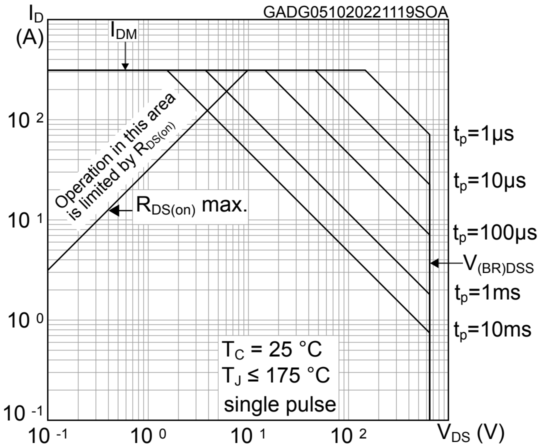


Figure 2. Maximum transient thermal impedance

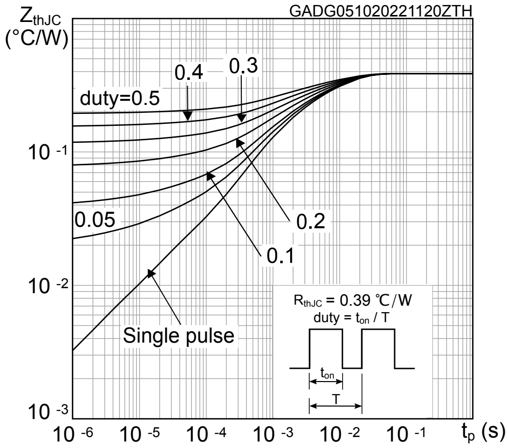


Figure 3. Typical output characteristics (T_J = 25 °C)

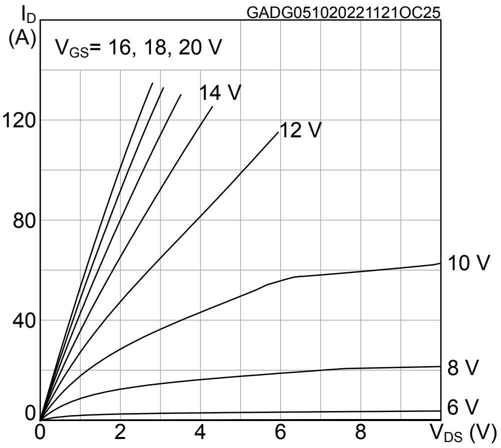


Figure 4. Typical output characteristics (T_J = 175 °C)

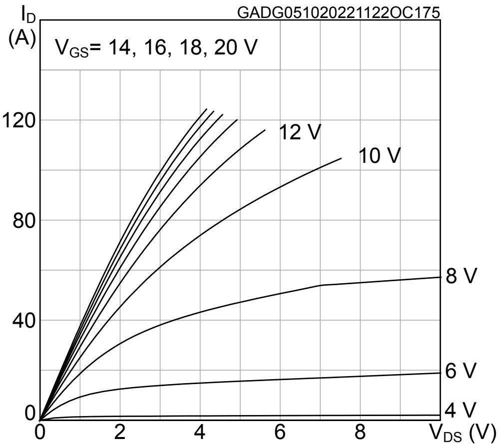


Figure 5. Typical transfer characteristics

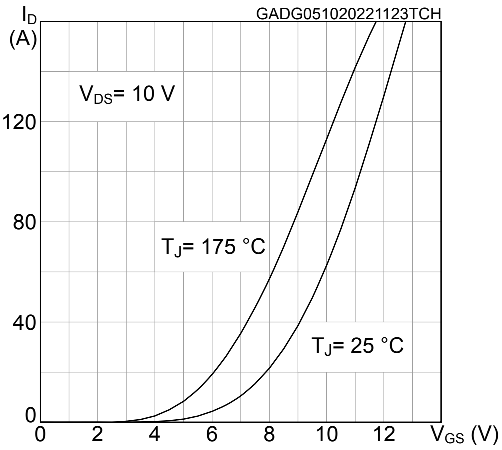


Figure 6. Total power dissipation

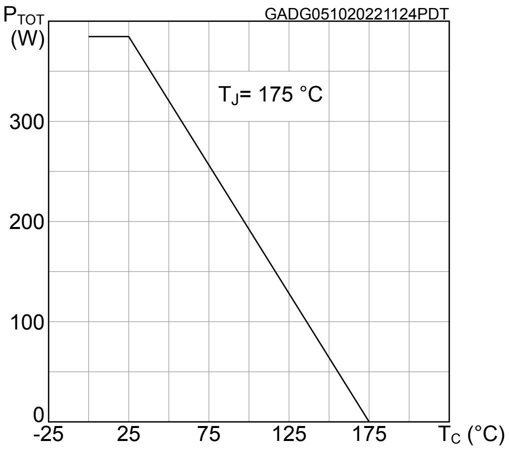


Figure 7. Typical gate charge characteristics

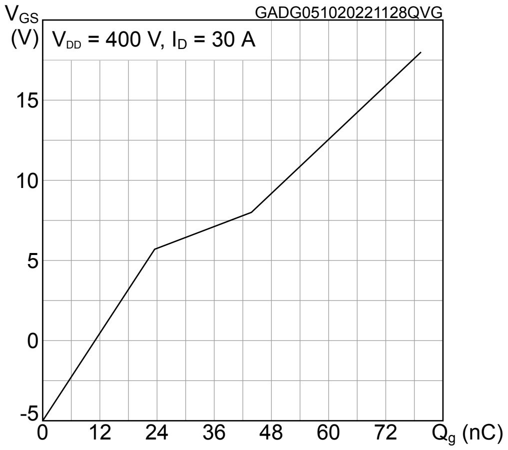


Figure 8. Typical capacitance characteristics

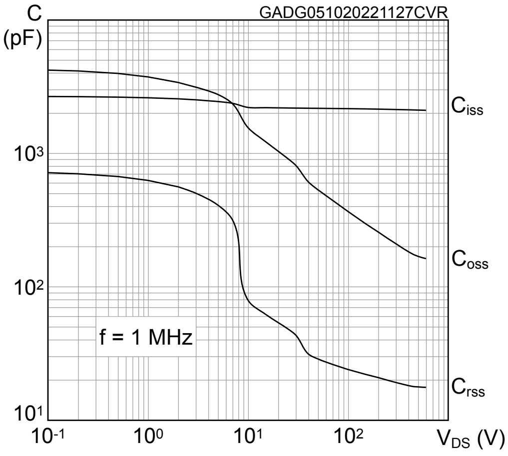


Figure 9. Typical switching energy vs drain current

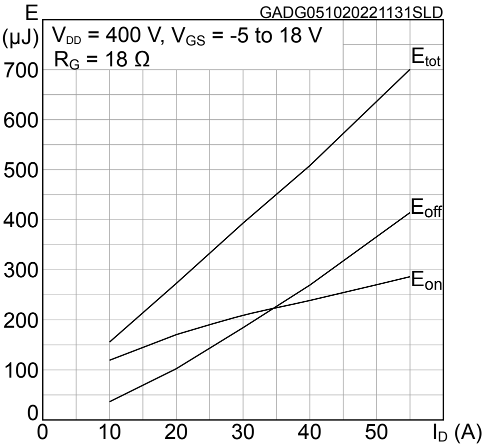


Figure 10. Typical switching energy vs supply voltage

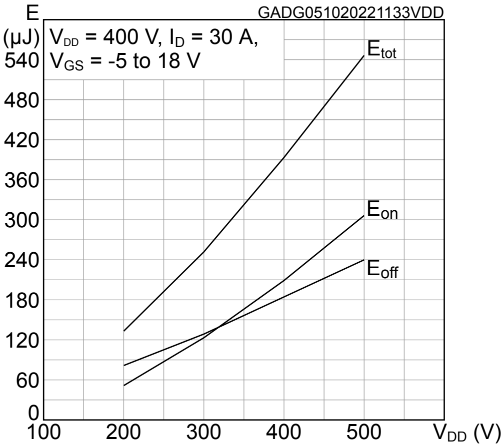


Figure 11. Typical switching energy vs gate resistance

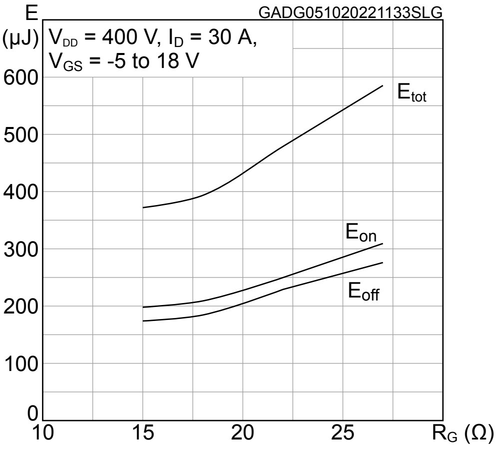


Figure 12. Normalized breakdown voltage vs temperature

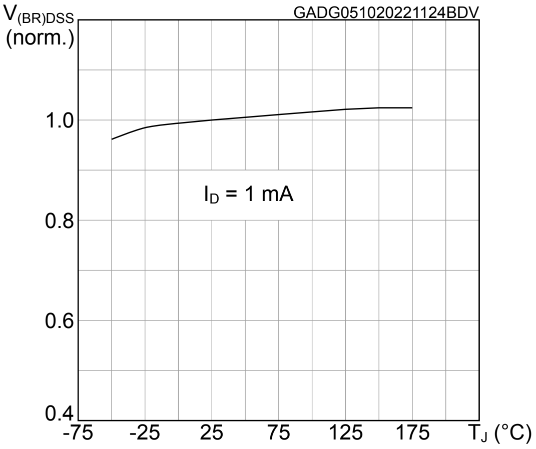


Figure 13. Normalized gate threshold vs temperature

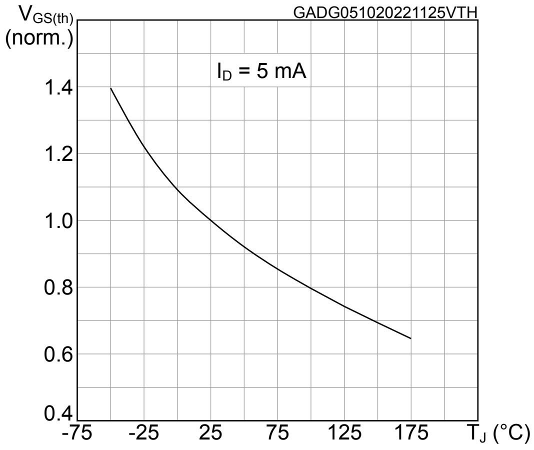


Figure 14. Normalized on-resistance vs temperature

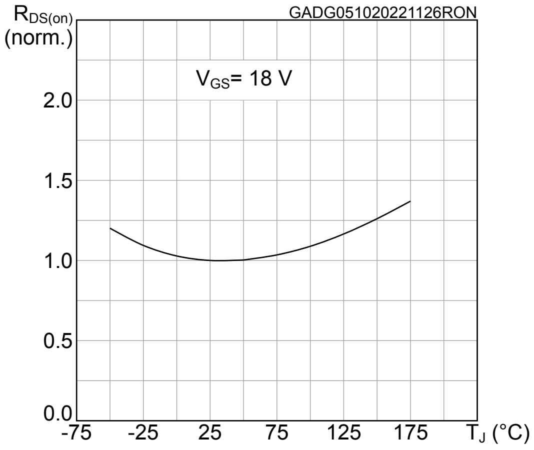


Figure 15. Typical reverse conduction characteristics (T_J = 25 °C)

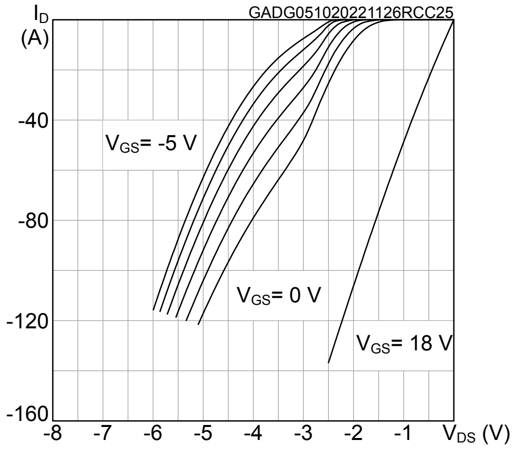
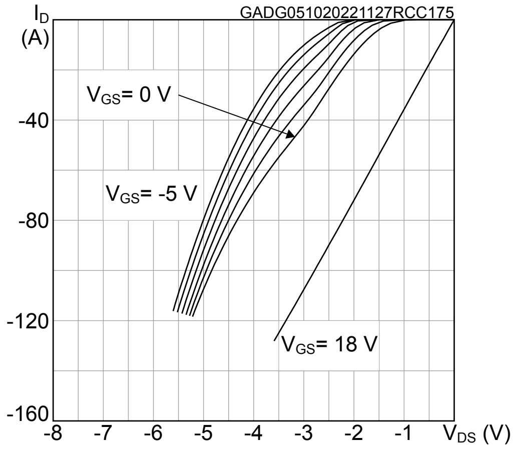


Figure 16. Typical reverse conduction characteristics (T_J= 175 °C)

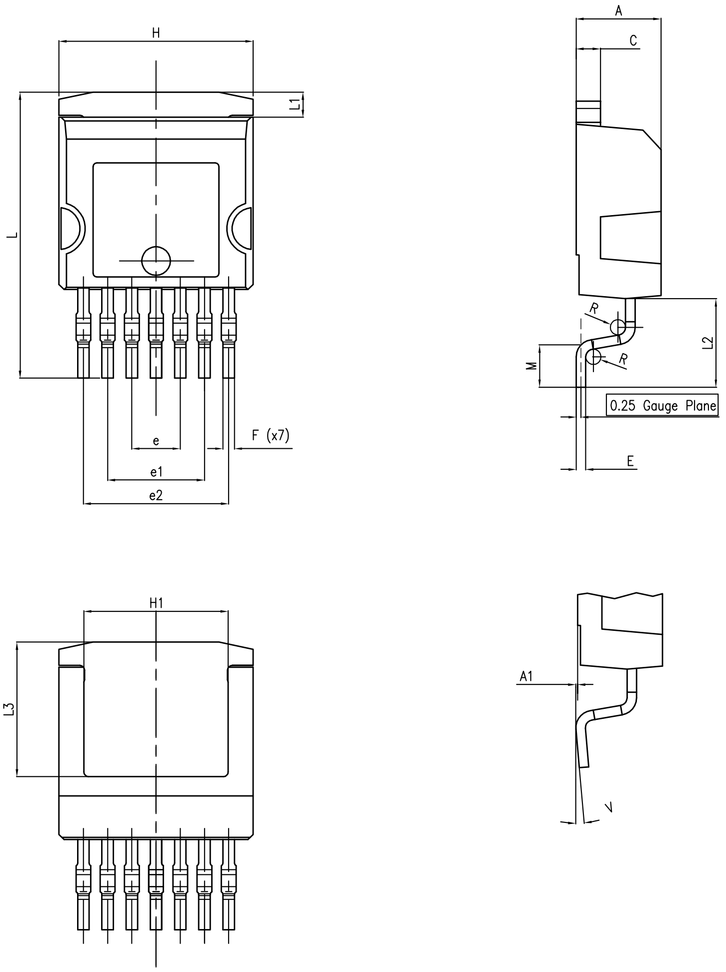


3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

3.1 H²PAK-7 package information

Figure 17. H²PAK-7 package outline

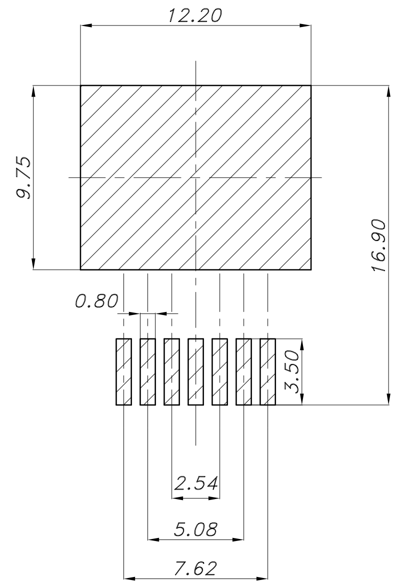


DM00249216_5

Table 8. **H^2PAK-7 package mechanical data**

Dim.	mm	
	Min.	Max.
A	4.30	4.80
A1	0.03	0.20
C	1.17	1.37
e	2.34	2.74
e1	4.88	5.28
e2	7.42	7.82
E	0.45	0.60
F	0.50	0.70
H	10.00	10.40
H1	7.40	8.00
L	14.75	15.25
L1	1.27	1.40
L2	4.35	4.95
L3	6.85	7.25
M	1.90	2.50
R	0.20	0.60
V	0°	8°

Figure 18. **H^2PAK-7 recommended footprint**



footprint_DM00249216_5

Note: Dimensions are in mm.

3.2 Packing information

Figure 19. Tape outline

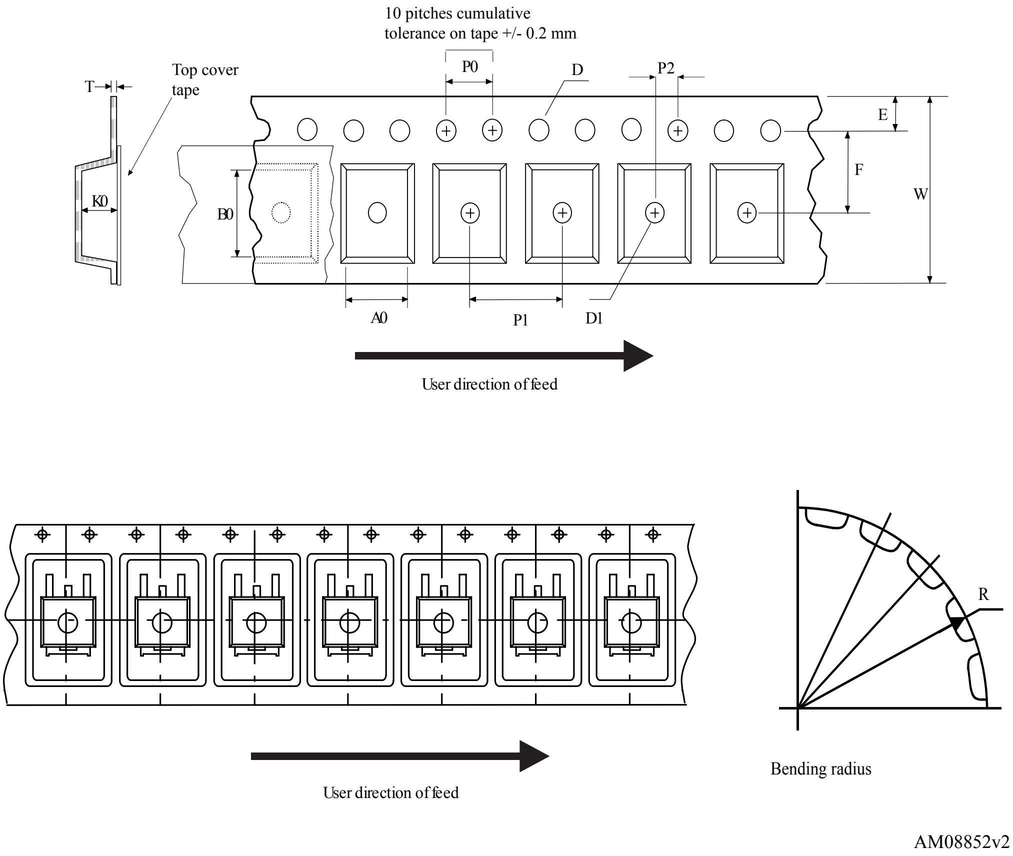


Figure 20. Reel outline

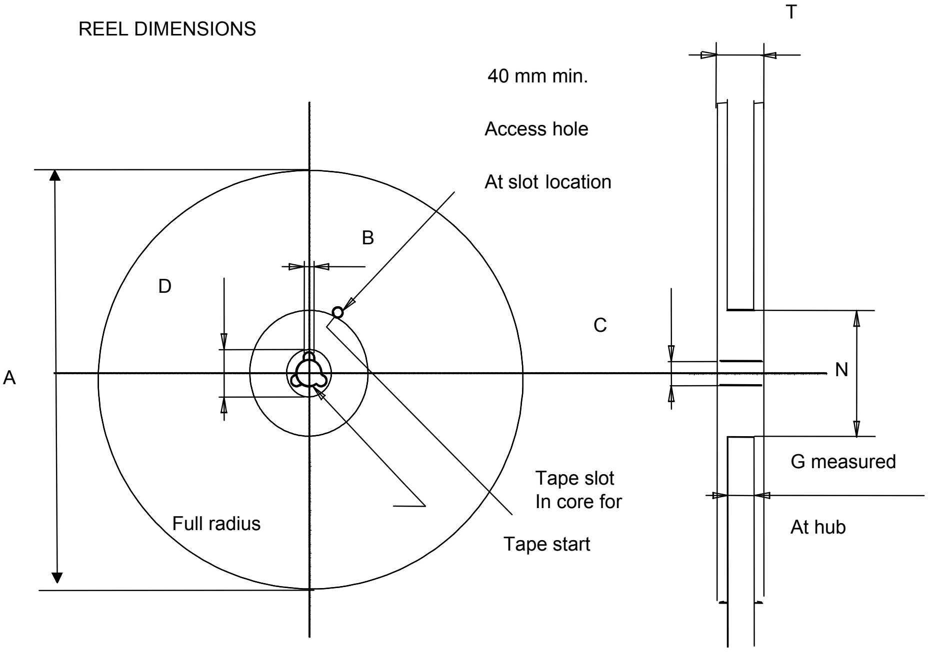


Table 9. **Tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Revision history

Table 10. **Document revision history**

Date	Revision	Changes
18-Aug-2023	1	First release.

Contents

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